

Digital Transistors (BRT)

R1 = 10 kΩ, R2 = ∞ kΩ

NPN Transistors with Monolithic Bias Resistor Network

MUN2215, MMUN2215L, MUN5215, DTC114TE, DTC114TM3, NSBC114TF3

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

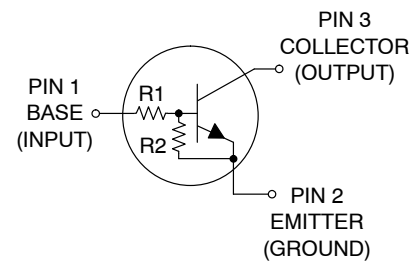
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

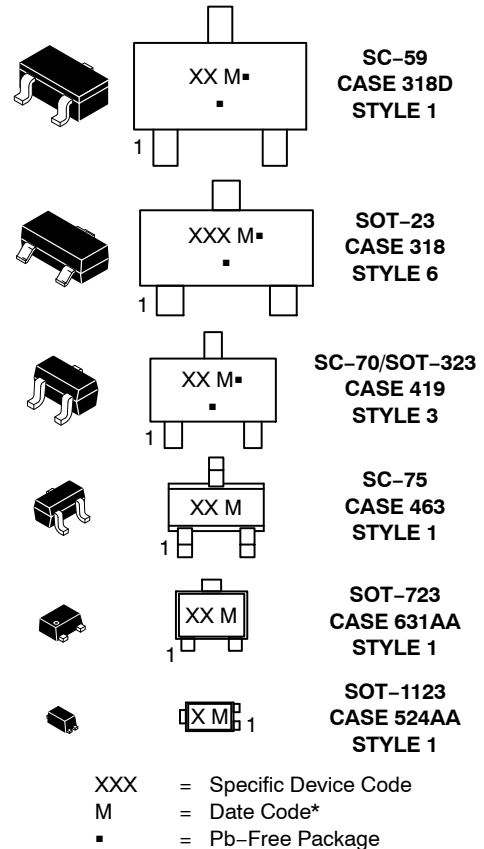
Rating	Symbol	Max	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current - Continuous	I _C	100	mAdc
Input Forward Voltage	V _{IN(fwd)}	40	Vdc
Input Reverse Voltage	V _{IN(rev)}	6	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

PIN CONNECTIONS



MARKING DIAGRAMS



(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking, and shipping information on page 2 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 2.

MUN2215, MMUN2215L, MUN5215, DTC114TE, DTC114TM3, NSBC114TF3

Table 1. ORDERING INFORMATION

Device	Part Marking	Package	Shipping†
MUN2215T1G	8E	SC-59 (Pb-Free)	3000 / Tape & Reel
MMUN2215LT1G, SMMUN2215LT1G*	A8E	SOT-23 (Pb-Free)	3000 / Tape & Reel
MUN5215T1G, SMUN5215T1G*	8E	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTC114TET1G	8E	SC-75 (Pb-Free)	3000 / Tape & Reel
DTC114TM3T5G	8E	SOT-723 (Pb-Free)	8000 / Tape & Reel

DISCONTINUED (Note 1)

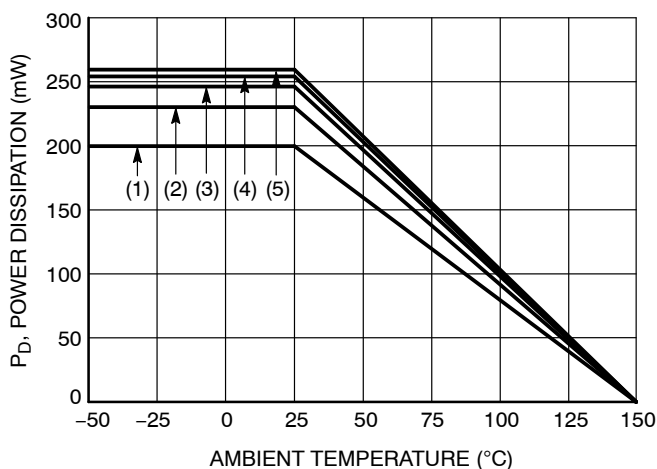
NSBC114TF3T5G	K (90°)	SOT-1123 (Pb-Free)	8000 / Tape & Reel
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†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

* (xx°) = Degree rotation in the clockwise direction.

1. **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on www.onsemi.com.



- (1) SC-75 and SC-70/SOT-323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm², 1 oz. copper trace
- (5) SOT-723; Minimum Pad

Figure 1. Derating Curve

MUN2215, MMUN2215L, MUN5215, DTC114TE, DTC114TM3, NSBC114TF3

Table 2. THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SC-59) (MUN2215)			
Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 2)	P_D	230	mW
Derate above 25°C (Note 3)		338	mW/°C
		1.8	
		2.7	
Thermal Resistance, Junction to Ambient (Note 2)	$R_{\theta JA}$	540	°C/W
(Note 3)		370	
Thermal Resistance, Junction to Lead (Note 2)	$R_{\theta JL}$	264	°C/W
(Note 3)		287	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C
THERMAL CHARACTERISTICS (SOT-23) (MMUN2215L)			
Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 2)	P_D	246	mW
Derate above 25°C (Note 3)		400	mW/°C
		2.0	
		3.2	
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	508	°C/W
(Note 3)		311	
Thermal Resistance, Junction to Lead (Note 2)	$R_{\theta JL}$	174	°C/W
(Note 3)		208	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C
THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5215)			
Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 2)	P_D	202	mW
Derate above 25°C (Note 3)		310	mW/°C
		1.6	
		2.5	
Thermal Resistance, Junction to Ambient (Note 2)	$R_{\theta JA}$	618	°C/W
(Note 3)		403	
Thermal Resistance, Junction to Lead (Note 2)	$R_{\theta JL}$	280	°C/W
(Note 3)		332	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C
THERMAL CHARACTERISTICS (SC-75) (DTC114TE)			
Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 2)	P_D	200	mW
Derate above 25°C (Note 3)		300	mW/°C
		1.6	
		2.4	
Thermal Resistance, Junction to Ambient (Note 2)	$R_{\theta JA}$	600	°C/W
(Note 3)		400	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C
THERMAL CHARACTERISTICS (SOT-723) (DTC114TM3)			
Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 2)	P_D	260	mW
Derate above 25°C (Note 3)		600	mW/°C
		2.0	
		4.8	
Thermal Resistance, Junction to Ambient (Note 2)	$R_{\theta JA}$	480	°C/W
(Note 3)		205	

2. FR-4 @ Minimum Pad.
3. FR-4 @ 1.0 x 1.0 Inch Pad.
4. FR-4 @ 100 mm², 1 oz. copper traces, still air.
5. FR-4 @ 500 mm², 1 oz. copper traces, still air.

MUN2215, MMUN2215L, MUN5215, DTC114TE, DTC114TM3, NSBC114TF3

Table 2. THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT-723) (DTC114TM3)			
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C
THERMAL CHARACTERISTICS (SOT-1123) (NSBC114TF3)			
Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 4)	P_D	254	mW
Derate above 25°C (Note 4)		297	mW/°C
		2.0	
		2.4	
Thermal Resistance, Junction to Ambient (Note 4)	$R_{\theta JA}$	493	°C/W
(Note 5)		421	
Thermal Resistance, Junction to Lead (Note 4)	$R_{\theta JL}$	193	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C

2. FR-4 @ Minimum Pad.
3. FR-4 @ 1.0 x 1.0 Inch Pad.
4. FR-4 @ 100 mm², 1 oz. copper traces, still air.
5. FR-4 @ 500 mm², 1 oz. copper traces, still air.

Table 3. ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Base Cutoff Current ($V_{CB} = 50\text{ V}, I_E = 0$)	I_{CBO}	-	-	100	nAdc
Collector-Emitter Cutoff Current ($V_{CE} = 50\text{ V}, I_B = 0$)	I_{CEO}	-	-	500	nAdc
Emitter-Base Cutoff Current ($V_{EB} = 6.0\text{ V}, I_C = 0$)	I_{EBO}	-	-	0.9	mAdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu\text{A}, I_E = 0$)	$V_{(BR)CBO}$	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 6) ($I_C = 2.0\text{ mA}, I_B = 0$)	$V_{(BR)CEO}$	50	-	-	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 6) ($I_C = 5.0\text{ mA}, V_{CE} = 10\text{ V}$)	h_{FE}	160	350	-	
Collector-Emitter Saturation Voltage (Note 6) ($I_C = 10\text{ mA}, I_B = 1.0\text{ mA}$)	$V_{CE(sat)}$	-	-	0.25	Vdc
Input Voltage (off) ($V_{CE} = 5.0\text{ V}, I_C = 100\ \mu\text{A}$)	$V_{i(off)}$	-	0.6	0.5	Vdc
Input Voltage (on) ($V_{CE} = 0.3\text{ V}, I_C = 10\text{ mA}$)	$V_{i(on)}$	1.7	1.2	-	Vdc
Output Voltage (on) ($V_{CC} = 5.0\text{ V}, V_B = 2.5\text{ V}, R_L = 1.0\text{ k}\Omega$)	V_{OL}	-	-	0.2	Vdc
Output Voltage (off) ($V_{CC} = 5.0\text{ V}, V_B = 0.25\text{ V}, R_L = 1.0\text{ k}\Omega$)	V_{OH}	4.9	-	-	Vdc
Input Resistor	R1	7.0	10	13	k Ω
Resistor Ratio	R_1/R_2	-	-	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

6. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle \leq 2%.

TYPICAL CHARACTERISTICS
MUN2215, MMUN2215L, MUN5215, DTC114TE, DTC114TM3

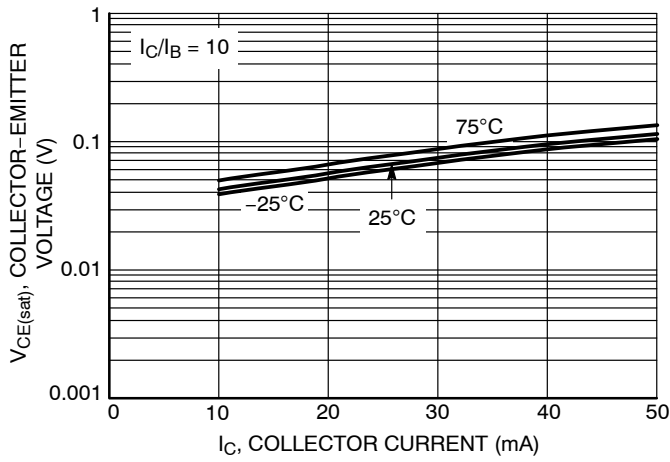


Figure 2. $V_{CE(sat)}$ vs. I_C

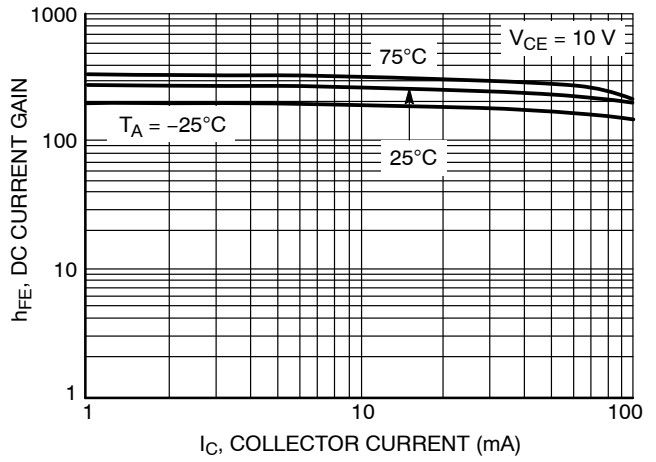


Figure 3. DC Current Gain

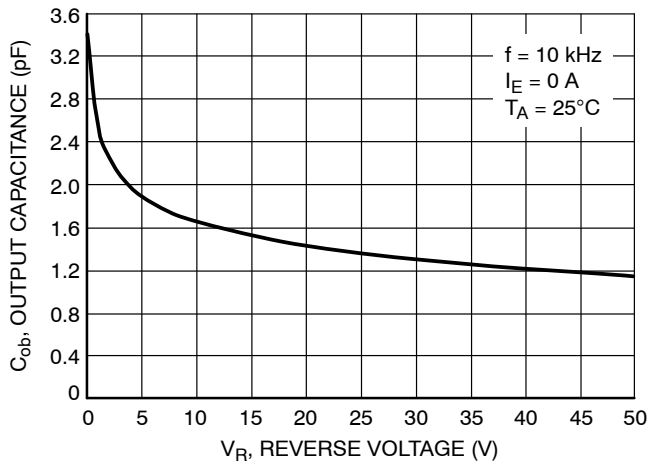


Figure 4. Output Capacitance

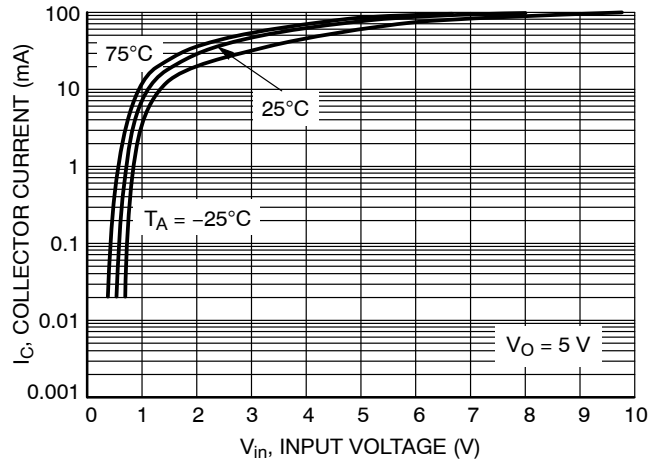


Figure 5. Output Current vs. Input Voltage

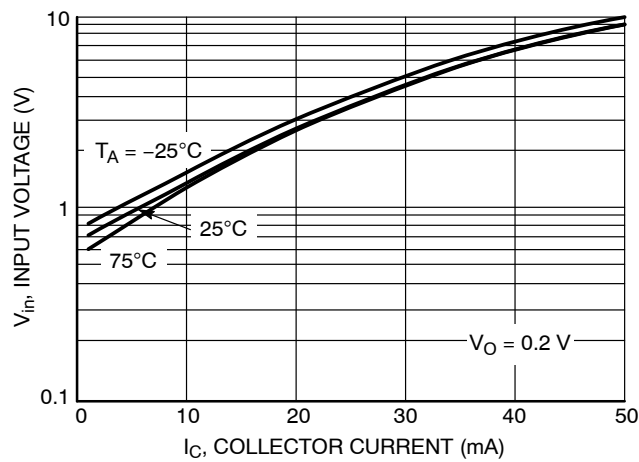


Figure 6. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS – NSBC114TF3

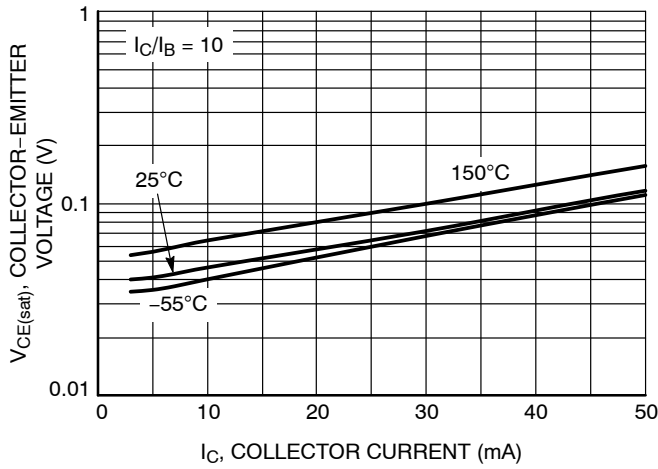


Figure 7. $V_{CE(sat)}$ vs. I_C

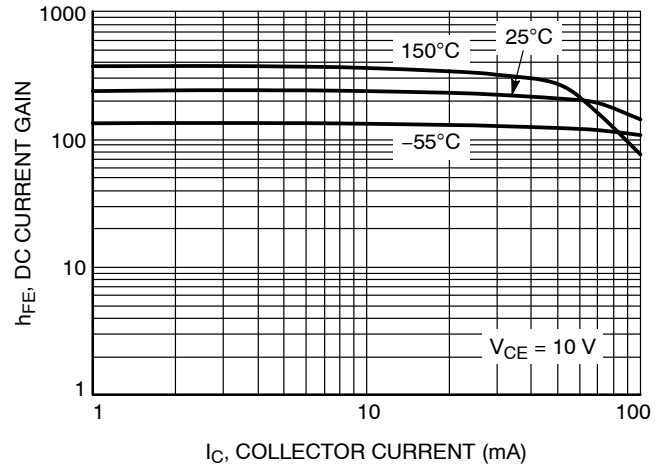


Figure 8. DC Current Gain

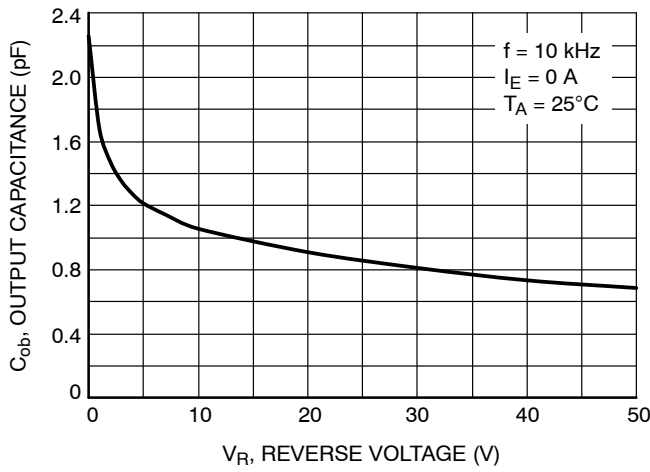


Figure 9. Output Capacitance

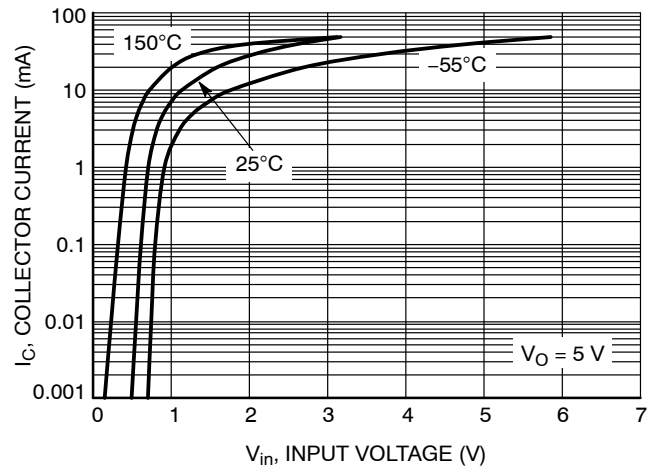


Figure 10. Output Current vs. Input Voltage

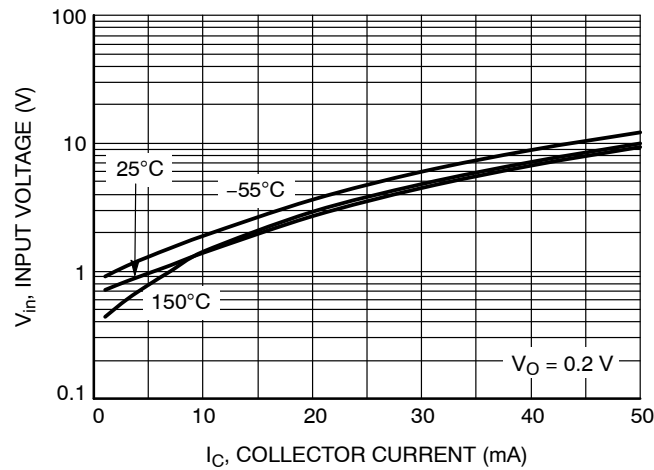


Figure 11. Input Voltage vs. Output Current

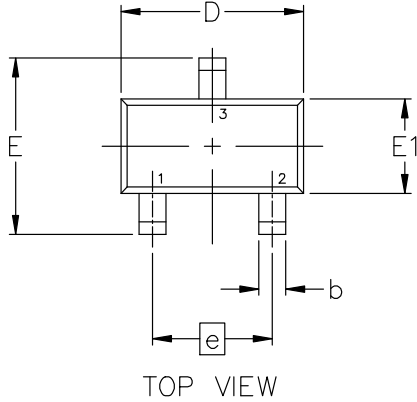
MUN2215, MMUN2215L, MUN5215, DTC114TE, DTC114TM3, NSBC114TF3

PACKAGE DIMENSIONS



SC-59-3 2.90x1.50x1.15, 1.90P
CASE 318D
ISSUE J

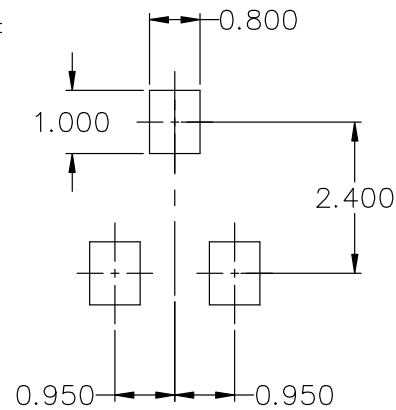
DATE 15 FEB 2024



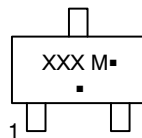
NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	1.00	1.15	1.30
A1	0.01	0.06	0.10
b	0.35	0.43	0.50
c	0.09	0.14	0.18
D	2.70	2.90	3.10
E	2.50	2.80	3.00
E1	1.30	1.50	1.70
e	1.90 BSC		
L	0.20	0.40	0.60



GENERIC MARKING DIAGRAM*



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package*

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

- STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR
- STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE
- STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE
- STYLE 4:
PIN 1. CATHODE
2. N.C.
3. ANODE
- STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE
- STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE/CATHODE

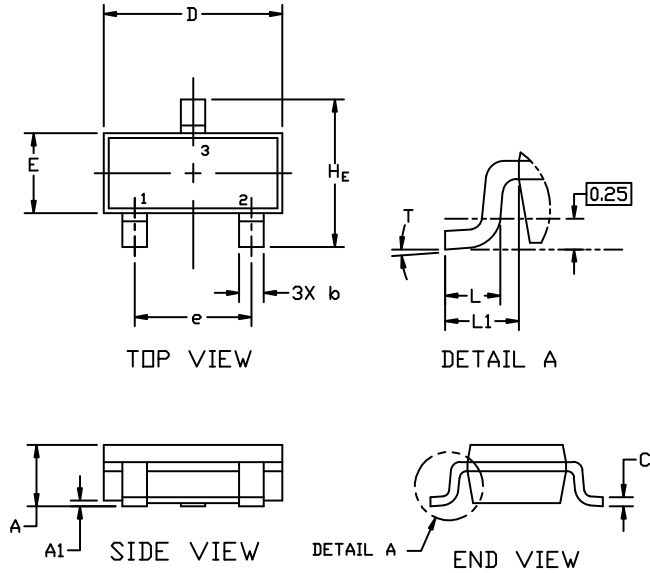
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SOT-23 (TO-236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

SCALE 4:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

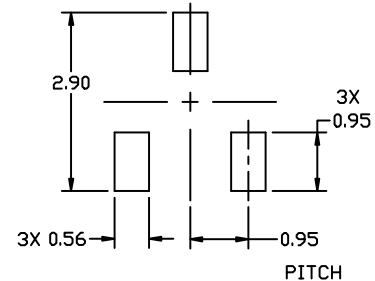
DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H _E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

GENERIC MARKING DIAGRAM*



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS



SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 4:1

SC-70 (SOT-323) CASE 419 ISSUE R

DATE 11 OCT 2022



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H _E	2.00	2.10	2.40	0.079	0.083	0.095

GENERIC MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

SOLDERING FOOTPRINT

- | | | | | | |
|-------------------------------------------------------|-------------------------------------------------------|-------------------------------------------------------|------------------------------------------------------------|-------------------------------------------------------------|---------------------------------------------------------|
| STYLE 1:
CANCELLED | STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE | STYLE 3:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE | STYLE 5:
PIN 1. ANODE
2. ANODE
3. CATHODE | |
| STYLE 6:
PIN 1. EMITTER
2. BASE
3. COLLECTOR | STYLE 7:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 8:
PIN 1. GATE
2. SOURCE
3. DRAIN | STYLE 9:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE | STYLE 10:
PIN 1. CATHODE
2. ANODE
3. ANODE-CATHODE | STYLE 11:
PIN 1. CATHODE
2. CATHODE
3. CATHODE |

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DESCRIPTION:	SC-70 (SOT-323)	PAGE 1 OF 1

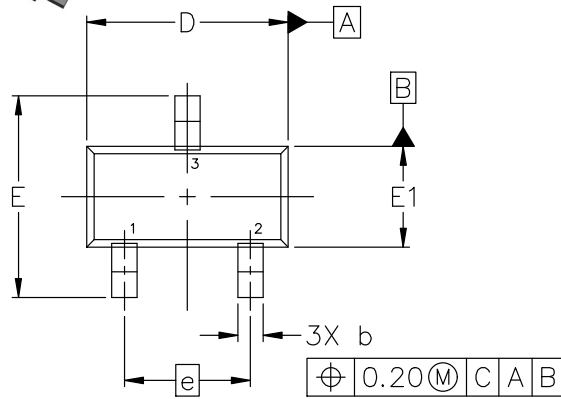
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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

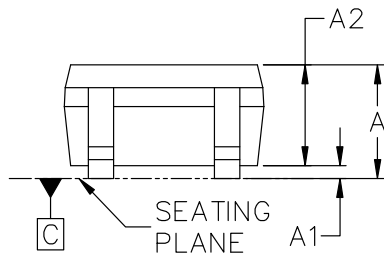


SC75-3 1.60x0.80x0.80, 1.00P
CASE 463
ISSUE H

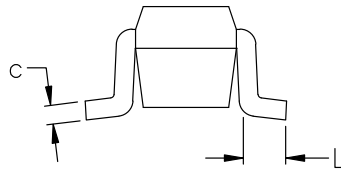
DATE 01 FEB 2024



TOP VIEW

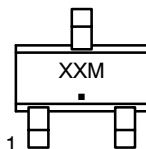


SIDE VIEW



END VIEW

GENERIC MARKING DIAGRAM*



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

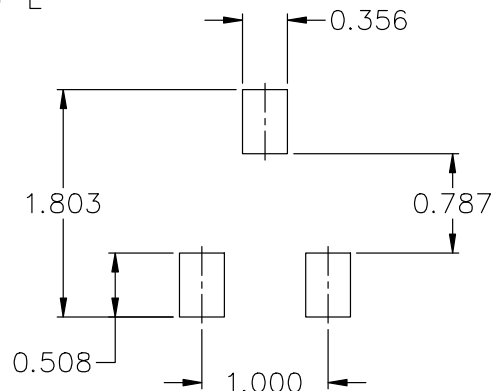
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

- | | | |
|-------------------------------------------------------|--------------------------------------------------|----------------------------------------------------|
| STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE | STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE |
| STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE | STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN | |

NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.80	0.90
A1	0.00	0.05	0.10
A2	0.80 REF.		
b	0.15	0.20	0.30
c	0.10	0.15	0.25
D	1.55	1.60	1.65
E	1.50	1.60	1.70
E1	0.70	0.80	0.90
e	1.00 BSC		
L	0.10	0.15	0.20



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS



SOT-1123 0.80x0.60x0.37, 0.35P
CASE 524AA
ISSUE D

DATE 18 JAN 2024



TOP VIEW



SIDE VIEW



BOTTOM VIEW

GENERIC MARKING DIAGRAM*



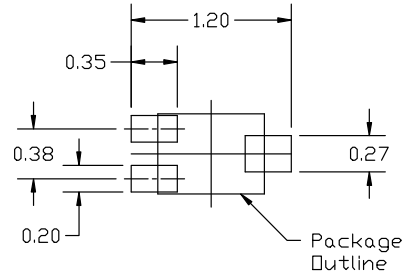
X = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.34	0.37	0.40
b	0.15	0.22	0.28
b1	0.10	0.15	0.20
c	0.07	0.12	0.17
D	0.75	0.80	0.85
E	0.55	0.60	0.65
e	0.35	0.38	0.40
H	0.950	1.000	1.050
L	0.185 REF		
L2	0.05	0.10	0.15



RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERM/D.

STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE	STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN
-------------------------------------------------------	--------------------------------------------------	----------------------------------------------------	------------------------------------------------------	--------------------------------------------------

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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



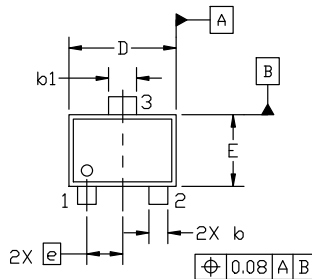
SOT-723 1.20x0.80x0.50, 0.40P
CASE 631AA
ISSUE E

DATE 24 JAN 2024

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
c	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25



TOP VIEW



SIDE VIEW



BOTTOM VIEW



RECOMMENDED MOUNTING FOOTPRINT

GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
2. EMITTER	2. N/C	2. ANODE	2. CATHODE	2. SOURCE
3. COLLECTOR	3. CATHODE	3. CATHODE	3. ANODE	3. DRAIN

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DESCRIPTION:	SOT-723 1.20x0.80x0.50, 0.40P	PAGE 1 OF 1

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